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(54) **THREE DIMENSIONAL (3D) MEMORY DEVICE AND FABRICATION METHOD**

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(57) **ABSTRACT**

A method for fabricating a 3D memory device includes forming a sacrificial layer over a substrate, forming a first dielectric stack over the sacrificial layer, forming a channel hole structure, forming an opening that exposes the sacrificial layer, removing the sacrificial layer to create a cavity and expose a part of the channel hole structure, forming a semiconductor layer to fill the cavity, filling the opening with a filling structure, and forming a second dielectric stack over the filling structure. The opening is made for a gate line slit (GLS) structure.